SCBS040A - JANUARY 1990 - REVISED JANUARY 1994

- BiCMOS Design Significantly Reduces ICCZ
- 3-State True Outputs Drive Bus Lines Directly
- High-Impedance State During Power Up and Power Down
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015
- Package Options Include Plastic Small-Outline (DW) Packages and Standard Plastic 300-mil DIPs (N)

## DW OR N PACKAGE (TOP VIEW)

DIR [	1	U	20	Vcc
A1 [	2		19	OE
A2 [	3		18	B1
A3 [	4		17	B2
A4 [	5		16	<b>B</b> 3
A5 [	6		15	] B4
A6 [	7		14	] B5
A7 [	8		13	] B6
A8 [	9		12	B7
GND [	10		11	] B8

## description

This octal bus transceiver is designed for asynchronous communication between data

buses. The devices transmit data from the A bus to the B bus or from the B bus to the A bus depending upon the logic level at the direction-control (DIR) input. The output-enable (OE) input can be used to disable the device so the buses are effectively isolated.

The outputs are in a high-impedance state during power up and power down while the supply voltage is less than approximately 3 V.

The SN64BCT245 is characterized for operation from -40°C to 85°C and 0°C to 70°C.

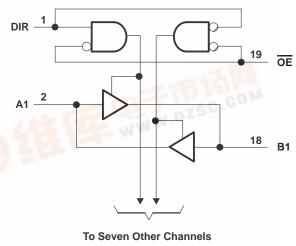
#### **FUNCTION TABLE**

INP	UTS	OPERATION
OE	DIR	OPERATION
L	L	B data to A bus
L	Н	A data to B bus
Н	X	Isolation

## logic symbol†

#### 19 OE G3 3EN1[BA] DIR 3EN2[AB] 18 В1 **A1** $\triangleleft$ 2∇ 17 **B2 A2** 4 16 **B3 A3** 5 15 **B4** Α4 14 **A5 B5** 13 **B6** Α6 12 8 A7 **B7** 11 **A8 B8**

# logic diagram (positive logic)



<sup>&</sup>lt;sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



# SN64BCT245 OCTAL BUS TRANSCEIVER WITH 3-STATE OUTPUTS

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## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>	– 0.5 V to 7 V
Input voltage range, V <sub>I</sub> (see Note 1)	– 0.5 V to 7 V
Voltage range applied to any output in the disabled or power-off state, V <sub>O</sub>	0.5 V to 5.5 V
Voltage range applied to any output in the high state, V <sub>O</sub>	$\dots - 0.5 \text{ V to V}_{CC}$
Current into any output in the low state	128 mA
Operating free-air temperature range	− 40°C to 85°C
Storage temperature range	. – 65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## recommended operating conditions

			MIN	NOM	MAX	UNIT
Vcc	Supply voltage			5	5.5	V
VIH	H High-level input voltage					V
VIL	IL Low-level input voltage				0.8	V
ΙΙΚ	Input clamp current				-18	mA
	A1-A8	A1-A8			-3	mA
ЮН	High-level output current	B1-B8			-15	ША
la.	Low lovel output ourrent	A1-A8			24	mA
IOL	Low-level output current B1-B8				64	IIIA
TA	Operating free-air temperature				85	°C



NOTE 1: The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER			TEST CONDITIONS				MAX	UNIT
VIK		V <sub>CC</sub> = 4.5 V,	I <sub>I</sub> = -18 mA				-1.2	V
VOH	Any A		I <sub>OH</sub> = -1 mA		2.5	3.4		
	Any A or B	V <sub>CC</sub> = 4.5 V	$I_{OH} = -3 \text{ mA}$		2.4	3.3		V
	Any B		I <sub>OH</sub> = -15 mA		2	3.1		
V	Any A	V 45V	I <sub>OL</sub> = 24 mA			0.35	0.5	V
VOL	Any B	V <sub>CC</sub> = 4.5 V	I <sub>OL</sub> = 64 mA			0.42	0.55	V
	Davisania	V 04000V	V <sub>O</sub> = 2.7 V	<u></u>			70	μΑ
	Power up	$V_{CC} = 0$ to 2.3 V	V <sub>O</sub> = 0.5 V	OE at 0.8 V			-0.65	mA
loz	Power down	V 4.0.V+= 0	V <sub>O</sub> = 2.7 V	<del></del>			70	μΑ
		$V_{CC} = 1.8 \text{ V to } 0$	V <sub>O</sub> = 0.5 V	OE at 0.8 V			-0.65	mA
ı <sub>l</sub> ‡	A and B	V 5.5.V	V <sub>I</sub> = 5.5 V				1	mA
	DIR and OE	V <sub>CC</sub> = 5.5 V,					0.1	
. +	A and B	V 55V	V: 0.7.V				70	^
I <sub>IH</sub> ‡	DIR and OE	V <sub>CC</sub> = 5.5 V,	V <sub>I</sub> = 2.7 V	V = 2.7 V			20	μΑ
	A and B	V 55V	V: 05.V				-0.65	A
IIL	DIR and OE	V <sub>CC</sub> = 5.5 V,	V <sub>I</sub> = 0.5 V				-1.2	mA
	Any A	V 55V	V <sub>O</sub> = 0		-60		-150	A
los§	Any B	V <sub>CC</sub> = 5.5 V,			-100		-225	mA
ICCH	A-to-B	V <sub>CC</sub> = 5.5 V				36	57	
ICCL	A-to-B	V <sub>CC</sub> = 5.5 V				57	90	mA
ICCZ		V <sub>CC</sub> = 5.5 V				10	15	
Ci	OE and DIR	V <sub>CC</sub> = 5 V,	V <sub>I</sub> = 2.5 V or 0.5 V			7		pF
0.	A to B	V 5.V	V: 05V:=05V	0.5.1/		9		
C <sub>io</sub>	B to A	V <sub>CC</sub> = 5 V,	V <sub>I</sub> = 2.5 V or 0.5 V			12		pF

## switching characteristics (see Note 2)

PARAMETER	FROM	TO	V <sub>CC</sub> = C <sub>L</sub> = S R1 = S R2 = S	50 pF, 500 Ω,	C <sub>L</sub> R1 R2	= 50 pF, = 500 Ω, = 500 Ω	,	<i>I</i> ,	UNIT		
	(INPUT)	(OUTPUT)	$T_A = 25^{\circ}C$		1 T 40°C   T 0°C		$= 25^{\circ}C$   $T_A = -40^{\circ}C$				
			MIN	MAX	MIN	MAX	MIN	MAX			
tpLH	A or B	B or A	1	6	1	7.2	1	7	ns		
t <sub>PHL</sub>		BUIA	1.5	6.6	1.5	7.6	1.5	7	115		
<sup>t</sup> PZH	ŌĒ	A or B	1.5	9.4	1.5	11.2	1.5	10.9	ns		
t <sub>PZL</sub>		AOIB	1.5	10.2	1.5	11.8	1.5	11.6	115		
<sup>t</sup> PHZ	ŌĒ	A or B	1.5	8.3	1.5	9.7	1.5	9.3	ns		
t <sub>PLZ</sub>	Ŭ.	AUB	1.5	7.8	1.5	9.6	1.5	9.1	115		

NOTE 2: Load circuits and voltage waveforms are shown in Section 1.



<sup>†</sup> All typical values are at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C. ‡ For I/O ports, the parameters I<sub>IH</sub> and I<sub>IL</sub> include the off-state output current. § Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

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